L Number	Hits	Search Text	DB	Time stamp
-	28	dram and (capacitor or capacitive or	USPAT;	2004/09/07 09:40
		capacitance) near8 (aluminum adj nitride or	US-PGPUB;	
		aln or al adj n)	EPO; JPO;	
			DERWENT;	
		[,,	IBM_TDB	
-	13	(dram or sdram or memory) and (capacitor or	USPAT;	2004/08/31 15:34
		capacitive or capacitance) near5 (dielectric	US-PGPUB;	
		or insulator or insulating) near5 (aluminum	EPO; JPO;	
		adj nitride or aln or al near2 n or al2n3)	DERWENT;	
_	23	(dram or sdram or memory) and (capacitor or	IBM_TDB USPAT;	2004/08/31 15:35
	23	capacitive or capacitance) near5 (dielectric	US-PGPUB;	2004/08/31 15:35
		or insulator or insulating) near5 (aluminum	EPO; JPO;	1
		near3 nitride or aln or al near2 n or al2n3)	DERWENT;	
			IBM TDB	i
-	23	(dram or sdram or memory) and (capacitor or	USPAT;	2004/08/31 15:39
		capacitive or capacitance) near5 (dielectric	US-PGPUB;	
		or insulator or insulating or spacer) near5	EPO; JPO;	
		(aluminum near3 nitride or aln or al near2 n	DERWENT;	-
		or al2n3)	IBM_TDB	
-	15	,	USPAT	2004/08/31 15:38
		"5599732" "5605858" "5650361"		
		"5656113" "5687112" "5709928"		
		"5767578" "5773882" "5783483"		
_	67	"5783716" "5786259" "5786635").PN.	HODAG	2004/00/22 25 :-
-	6/	(capacitor or capacitive or capacitance or storage) near5 (dielectric or insulator or	USPAT;	2004/08/31 15:41
		insulating or spacer) near5 (aluminum near3	US-PGPUB; EPO; JPO;	
		nitride or aln or al near2 n or al2n3)	DERWENT;	
		nitified of aim of all hears in of allship	IBM TDB	
-	75	(capacitor or capacitive or capacitance or	USPAT;	2004/08/31 16:21
		storage) near5 (dielectric or insulator or	US-PGPUB;	2001, 00, 31 20.22
		insulating or spacer) near5 (aluminum near3	EPO; JPO;	
		nitride or aln or al near2 n or al2n3 or	DERWENT;	
		nitride near3 Al)	IBM_TDB	
-	64	(capacitor or capacitive or capacitance or	USPAT;	2004/08/31 16:22
		storage) near5 (dielectric or insulator or	US-PGPUB;	
		insulating or spacer) near5 (metal near2	EPO; JPO;	
		nitride)	DERWENT;	
_	898	257/210 cclc	IBM_TDB	2004/20/21 20 50
_	098	257/310.ccls.	USPAT;	2004/09/01 08:50
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
- 1	110	257/310.ccls. and (aluminum near3 nitride or	USPAT;	2004/09/01 08:51
		al near3 nitride or aln or al near2 n or	US-PGPUB;	
		"al2n3")	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	111	257/310.ccls. and (aluminum near3 nitride or	USPĀT;	2004/09/01 08:52
	i	al near3 nitride or aln or al near2 n or	US-PGPUB;	
		"al2n3" or alno or alon or aluminum near3	EPO; JPO;	
ļ		oxynitride or nitrided near2 alumina)	DERWENT;	
		057/010 0010 000 100	IBM_TDB	2221152155
-	111	257/310.ccls. and (aluminum near3 nitride or	USPAT;	2004/09/01 09:40
		al near3 nitride or aln or al near2 n or "al2n3" or alno or alon or aluminum near3	US-PGPUB;	
		oxynitride or nitrided near2 alumina or	EPO; JPO;	
		nitride near alumina)	DERWENT; IBM TDB	
_	14	("4455568" "5032892" "5079609"	USPAT	2004/09/01 09:11
ļ	, }	"5212402" "5266821" "5366931"	35131	2004/05/01 03:11
ı		"5656834" "5668399" "5932905"		
,		"5940676"		
		"5973908" "6034391").PN.		
-	1576	(dram or sdram or memory) and (insulator or	USPAT;	2004/09/01 09:42
		insulating or dielectric) near6 ((aluminum	US-PGPUB;	,,
		or alumina or al) near4 (nitride or n or	EPO; JPO;	
		nitrided or oxynitride) or aln)	DERWENT;	
1			IBM TDB	

	004/09/01 09:43
or dielectric) near5 ((aluminum or alumina US-PGPUB;	
or al) near3 (nitride or n or nitrided or EPO; JPO;	
oxynitride) or aln) DERWENT;	
IBM_TDB	
	004/09/01 10:26
or dielectric) near5 ((aluminum or alumina US-PGPUB; or al) near3 (nitride or n or nitrided or EPO; JPO;	
oxynitride) or aln) near15 (capacitor or DERWENT; capacitive or capacitance) IBM TDB	
	004/09/01 10:37
6358810.pn. 5183684.pn. 6372530.pn. US-PGPUB;	004/03/01 10:37
6072211.pn. EPO; JPO;	
DERWENT;	
IBM TDB	
	004/09/01 10:39
spacer or dielectric) near8 ((aluminum or US-PGPUB;	. ,
alumina or al) near8 (nitride or nitrided or EPO; JPO;	
nitrate or n or oxynitride or oxinitride or DERWENT;	
oxy-nitride or nitridation or nitrdation) or IBM_TDB	
aln or al2n3 or alon or alxny)	
	004/09/01 10:41
spacer or dielectric) near8 ((aluminum or US-PGPUB;	
alumina or al) near8 (nitride or nitrided or EPO; JPO;	
nitrate or n or oxynitride or oxinitride or DERWENT;	
oxy-nitride or nitridation or nitrdation) or IBM_TDB	
aln or al2n3 or alon or alxny) - 76 257/296.ccls. and (insulator or insulating USPAT; 2	004/00/01 11 55
or spacer or dielectric) near8 ((aluminum or US-PGPUB;	004/09/01 11:56
alumina or al) near8 (nitride or nitrided or EPO; JPO;	
nitrate or n or oxynitride or oxinitride or DERWENT;	
oxy-nitride or nitridation or nitrdation) or IBM TDB	
aln or al2n3 or alon or alno or alxny)	
	004/09/01 11:05
"6531750" "6548871").PN.	, ,
- 10 257/298.ccls. and (insulator or insulating USPAT; 2	004/09/01 11:58
or spacer or dielectric) near8 ((aluminum or US-PGPUB;	
alumina or al) near8 (nitride or nitrided or EPO; JPO;	
nitrate or n or oxynitride or oxinitride or DERWENT;	
oxy-nitride or nitridation or nitrdation) or IBM_TDB	
aln or al2n3 or alon or alxny)	221/22/22 22 22
	004/09/01 12:08
alumina or al) near8 (nitride or nitrided or EPO; JPO; nitrate or n or oxynitride or oxinitride or DERWENT;	
oxy-nitride or nitridation or nitrdation) or IBM_TDB	
aln or al2n3 or alon or alno or alxny)	
	004/09/01 12:05
	004/09/01 12:17
or spacer or dielectric) near8 ((aluminum or US-PGPUB;	
alumina or al) near8 (nitride or nitrided or EPO; JPO;	
nitrate or n or oxynitride or oxinitride or DERWENT;	
oxy-nitride or nitridation or nitrdation) or IBM_TDB	
aln or al2n3 or alon or alxny)	001/00/00
	004/09/01 12:19
or spacer or dielectric) near8 ((aluminum or US-PGPUB;	
alumina or al) near8 (nitride or nitrided or EPO; JPO; nitrate or n or oxynitride or oxinitride or DERWENT;	
nitrate or n or oxynitride or oxinitride or DERWENT; oxy-nitride or nitridation or nitrdation) or IBM TDB	
aln or al2n3 or alon or alxny)	
	004/09/01 12:22
or spacer or dielectric) near8 ((aluminum or US-PGPUB;	
alumina or al) near8 (nitride or nitrided or EPO; JPO;	
nitrate or n or oxynitride or oxinitride or DERWENT;	
oxy-nitride or nitridation or nitrdation) or IBM_TDB	
aln or al2n3 or alon or alno or alxny)	
	004/09/01 12:46
or spacer or dielectric) near8 ((aluminum or US-PGPUB;	
alumina or al) near8 (nitride or nitrided or EPO; JPO;	
nitrate or n or oxynitride or oxinitride or DERWENT;	

			,	
-	6	257/305.ccls. and (insulator or insulating	USPAT;	2004/09/01 12:47
		or spacer or dielectric) near8 ((aluminum or	US-PGPUB;	
		alumina or al) near8 (nitride or nitrided or	EPO; JPO;	
		nitrate or n or oxynitride or oxinitride or	DERWENT;	
		oxy-nitride or nitridation or nitrdation) or	IBM_TDB	
		aln or al2n3 or alon or alno or alxny)		
-	66	257/306.ccls. and (insulator or insulating	USPAT;	2004/09/01 13:05
		or spacer or dielectric) near8 ((aluminum or	US-PGPUB;	
		alumina or al) near8 (nitride or nitrided or	EPO; JPO;	
		nitrate or n or oxynitride or oxinitride or	DERWENT;	
		oxy-nitride or nitridation or nitrdation) or	IBM_TDB	
		aln or al2n3 or alon or alno or alxny)	_	
-	8	257/311.ccls. and (insulator or insulating	USPAT;	2004/09/01 13:08
		or spacer or dielectric) near8 ((aluminum or	US-PGPUB;	
	İ	alumina or al) near8 (nitride or nitrided or	EPO; JPO;	
		nitrate or n or oxynitride or oxinitride or	DERWENT;	
1		oxy-nitride or nitridation or nitrdation) or	IBM TDB	
	}	aln or al2n3 or alon or alno or alxny)	_	
_	50	257/532.ccls. and (insulator or insulating	USPAT;	2004/09/01 13:10
		or spacer or dielectric) near8 ((aluminum or	US-PGPUB;	
		alumina or al) near8 (nitride or nitrided or	EPO; JPO;	
1		nitrate or n or oxynitride or oxinitride or	DERWENT;	
		oxy-nitride or nitridation or nitrdation) or	IBM TDB	
]	aln or al2n3 or alon or alno or alxny)		
-	120		USPAT;	2004/09/07 10:18
1	120	(capacitor or capacitance or capacitive)	US-PGPUB;	2004/03/01 10:10
1	1	near8 (dielectric or insulator or insulating	EPO; JPO;	
		or spacer or insulative) near8 (alumina or		
		aluminum near2 oxide or al near2 o or alo or	DERWENT;	
		aluminum near nitride or al near2 n or aln)	IBM_TDB	
_	15		110D3m	2004/00/05 00 50
1	15	("5183684" "5356608" "5573742"	USPAT	2004/09/07 09:59
		"5599732" "5605858" "5650361"		
		"5656113" "5687112" "5709928"		
		"5767578" "5773882" "5783483"		
	6.3	"5783716" "5786259" "5786635").PN.		
-	61	memory near8 (capacitor or capacitance) and	USPAT;	2004/09/07 14:14
		(capacitor or capacitance or capacitive)	US-PGPUB;	
		near8 (dielectric or insulator or insulating	EPO; JPO;	
		or spacer or insulative) near8 (metal near2	DERWENT;	
	İ .	nitride)	IBM_TDB	
-	4	("4058430" "4861417" "5166092"	USPAT	2004/09/07 10:30
İ		"5256244").PN.		
-	81	(capacitor or capacitance) near3 (dielectric	USPAT;	2004/09/07 15:13
		or insulator or diel or insulating or	US-PGPUB;	
		insulative or ins or spacer or gap) near10	EPO; JPO;	
		(aluminum near3 nitride or aln or al near2	DERWENT;	
		n)	IBM_TDB	
ļ	8	("5525542" "5578523" "5652176"	USPAT	2004/09/07 14:25
		"5674771" "5734177" "5812364"		
		"6255187" "6329234").PN.		
-	1	"5789320".PN.	USPAT	2004/09/07 14:32
-	29	US-5656113-\$.DID. OR US-5709928-\$.DID. OR	USPAT;	2004/09/07 15:15
		US-5605858-\$.DID. OR US-5687112-\$.DID. OR	US-PGPUB;	
		US-5767578-\$.DID. OR US-5773882-\$.DID. OR	EPO; JPO;	į
		US-5783483-\$.DID. OR US-5783716-\$.DID. OR	DERWENT;	
		US-5786635-\$.DID. OR US-5786259-\$.DID. OR	IBM TDB	
		US-5183684-\$.DID. OR US-5356608-\$.DID. OR		
		US-5573742-\$.DID. OR US-5599732-\$.DID. OR		
		US-5650361-\$.DID.		
-	4	6294420.pn. 6307775.pn.	USPAT;	2004/09/07 15:23
			US-PGPUB;	-202, 02, 07, 13.23
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	2	6358810.pn.	USPAT;	2004/09/07 15:37
1		, 000010.pm.	US-PGPUB;	2004/03/0/ 15:3/
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	L _

-	6	6181056.pn. 6218771.pn. 6459096.pn.	USPAT;	2004/09/07 15:40
			US-PGPUB;	
			EPO; JPO;	
ŀ			DERWENT;	
			IBM_TDB	
-	2	6072211.pn.	USPAT;	2004/09/07 15:43
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	2	6218293.pn.	USPAT;	2004/09/07 15:43
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	